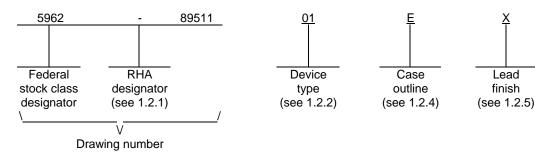
								ı	REVISI	ONS										
LTR						DESCF	RIPTIO	N					DA	ATE (Y	R-MO-I	DA)		APPF	ROVED	
А	section	on. Ch	ange m	F and 2. Add output noise voltage test to teminimum limit for VTH(SYNC) test in table changes throughout.						nce	94-02-28		M. A. FRYE							
В	Add	device	class V	/ device	e and n	nake cł	nange t	o TABI	_E II	ro				00-1	1-30		R. MONNIN			
С		device e 2 ı		5. Mak	e Char	nges to	1.2.2,	1.3, 1.4	, table	l, figure	1, and	I		01-0	3-21		R. MONNIN			
D	Draw	ing upo	dated to	o reflec	t curre	nt requ	iremen	ts. –rr)					06-0	3-13			R. M	NINNC	
THE ORIGINAL	. FIRST	SHEE	T OF T	THIS DI	RAWIN	IG HAS	S BEEN	I REPL	ACED.											
	. FIRST	SHEE	T OF T	THIS DI	RAWIN	IG HAS	S BEEN	I REPL	ACED.	T			Г	T	Γ				T	
REV	. FIRST	SHEE	T OF T	THIS DI	RAWIN	IG HAS	S BEEN	REPL	ACED.											
REV SHEET	FIRST	SHEE	T OF T	THIS DI	RAWIN	IG HAS	S BEEN	REPL	ACED.											
REV SHEET REV	FIRST	SHEE	T OF T	THIS DI	RAWIN	IG HAS	SBEEN	REPL	ACED.											
REV SHEET REV SHEET	FIRST	SHEE	T OF T			IG HAS		REPL	ACED.	D	D	D	D	D	D	D	D	D	D	D
REV SHEET REV	FIRST	SHEE	T OF T	REV	(IG HAS	BEEN D 1				D 5	D 6	D 7	D 8	D 9	D 10	D 11	D 12	D 13	D 14
REV SHEET REV SHEET REV STATUS	FIRST	SHEE	T OF T	REV SHE	/ EET		D 1	D	D	D	5	6	7		9	10	11	12	13	
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A	NDAF	RD	T OF T	REV SHE PRE J	/ EET PAREI OSEP	D BY H A. KE	D 1	D	D	D	5	6 EFEN	7 SE SI	8	9 Y CE	10 NTER O 432	11 R COL 218-3	12 -UMB	13	
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STAT MICRO DRA THIS DRAWIN FOR US DEPAR	NDAF OCIRC WING IG IS A SE BY A	RD CUIT G VAILAI	BLE	REV SHE PRE J	PAREI OSEP CKED D. H. JO	D BY H A. KE BY DHNSC D BY EL A. F	D 1 ERBY ON	D 2	D	D 4	DI DI	EFEN CC	SE SI DLUM http:	UPPL IBUS,	y CE, OHIO	INTER O 433 scc.dl	11 R COL 218-3: a.mil	12 LUMB 990	us PULS	14
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STAT MICRO DRA THIS DRAWIN FOR US	NDAF OCIRO WING IG IS A SE BY A STMEN ICIES (C	RD CUIT G VAILAI ALL TS DF THE	BLE	REV SHE PRE J	PAREI OSEP CKED D. H. JO	D BY H A. KE BY DHNSC D BY EL A. F	D 1 ERBY ON	D 2	D	D 4	DI DI	EFEN CC	SE SI DLUM http:	UPPLIBUS, o://ww	y CE, OHIO	INTER O 433 scc.dl	11 R COL 218-3: a.mil	12 LUMB 990	us PULS	14
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STAT MICRO DRA THIS DRAWIN FOR US DEPAR AND AGEN DEPARTMEN	NDAF OCIRO WING IG IS A SE BY A STMEN ICIES (C	RD CUIT G VAILAI ALL TS DF THE DEFEN	BLE	REV SHE PRE J CHE	CKED D. H. JO PROVE	D BY H A. KE BY DHNSC D BY EL A. F	D 1 ERBY ON ERYE OVAL C	D 2	D	D 4 MIC WIE	DI DI	EFEN CO	SE SI DLUM http:	BUPPLIBUS, D://www	y CE, OHIO	10 ENTER O 432 GCC.dl	11 R COL 218-33 a.mil	12 LUMB 990	us PULS	14

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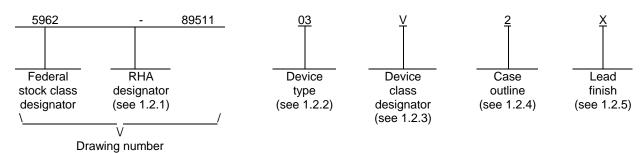
1. SCOPE

- 1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.
 - 1.2 PIN. The PIN is as shown in the following examples.

For device classes M and Q:



For device class V:



- 1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 <u>Device type(s)</u>. The device type(s) identify the circuit function as follows:

Device type	Generic number	<u>Circuit function</u>
01	1525A	Regulating pulse width modulator
02	1527A	Regulating pulse width modulator
03	UC1525A	Regulating pulse width modulator
04	UC1527A	Regulating pulse width modulator
05	UC1525B	Regulating pulse width modulator

1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as listed below. Since the device class designator has been added after the original issuance of this drawing, device classes M and Q designators will not be included in the PIN and will not be marked on the device.

<u>Device class</u>	Device requirements documentation
М	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A
Q or V	Certification and qualification to MIL-PRF-38535

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1.2.4 <u>Case outline(s)</u>. The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	<u>Descriptive designator</u>	<u>Terminals</u>	Package style
E	GDIP1-T16 or CDIP2-T16	16	Dual-in-line
F	GDFP2-F16 or CDFP3-F16	16	Flat pack
2	CQCC1-N20	20	Square leadless chip carrier

1.2.5 <u>Lead finish</u>. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

1.3 Absolute maximum ratings. 1/

Input voltage (+V _{IN})	+40 V dc
Collector voltage (V _C)	+40 V dc
Logic inputs range	-0.3 V dc to +5.5 V dc
Analog inputs range	$-0.3 \text{ V dc to } +\text{V}_{\text{IN}}$
Output current, source or sink	
Reference output current	50 mA
Oscillator charging current	5 mA
Maximum power dissipation (P _D)	· ·
Lead temperature (soldering, 10 seconds)	+300°C
Junction temperature (T _J)	+150°C
Storage temperature range	-65°C to +150°C
Thermal resistance, junction-to-case ($\theta_{\mbox{\scriptsize JC}}$)	See MIL-STD-1835
Thermal resistance, junction-to-ambient (θ_{JA}):	
Cases E and F	
Case 2	70°C/W

1.4 Recommended operating conditions.

Input voltage (+V _{IN})	+8 V dc to +35 V dc
Collector voltage (V _C)	+4.5 V dc to +35 V dc
Sink/source load current (steady-state)	
Sink/source load current (peak)	0 mA to 400 mA
Reference load current range	0 mA to 20 mA
Oscillator frequency range:	
Device types 01 - 04	
Device type 05	100 Hz to 400 kHz
Oscillator timing resistor (R _T):	
Device types 01 – 04	2 k Ω to 200 k Ω
Device type 05	2 k Ω to 150 k Ω
Oscillator timing capacitor range (C _T):	
Device types 01 – 04	470 pF to 0.1 μF
Device type 05	0.001 pF to 0.1 μF
Dead time resistor range (device type 05 only)	0 Ω to 500 Ω
Ambient operating temperature range (T _A)	-55°C to +125°C

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^{1/} Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at http://assist.daps.dla.mil/quicksearch/ or http:

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.
 - 3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.
 - 3.2.3 Logic diagrams. The logic diagrams shall be as specified on figure 2.
- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.
- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.
- 3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

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	T.	ABLE I. Electrical performanc	e characteristic	<u>s</u> .			
Test	Symbol	Conditions $\underline{1}/$ -55°C \leq T _A \leq +125°C unless otherwise specified	Group A subgroups	Device type	Limi	its <u>2</u> /	Unit
Reference section					IVIIII	IVIAX	<u> </u>
Reference voltage out	V _{REF}		1	01-04	5.05	5.15	V
			2,3	-	5.0	5.2	-
			1	05	5.062	5.138	-
Line regulation	V _{RLINE}	V _{IN} = 8 V to 35 V	1,2,3	01-04	-30	30	mV
				05	-10	10	1
Load regulation	V _{LOAD}	I _L = 0 mA to 20 mA	1,2,3	01-04	-50	50	mV
				05	-15	15	1
Short-circuit current	los	V _{REF} = 0 V, t < 25 ms,	1	01-04	-100		mA
		T _A = +25°C		05		100	-
Temperature stability	VTS	<u>3</u> /	2,3	05		50	mV
Total output variation	V _{TOV}	Line, load, and temperature	1,2,3	05	5.036	5.164	V
Long term stability	V _{LTS}	1000 hours, $3/$ T _A = +125°C	2	05		10	mV
Output noise voltage	No	10 Hz \leq f \leq 10 kHz, $3/$ T _A = +25°C	7	All		200	μVrms
Oscillator section				_			
Initial accuracy	Fosc	T _A = +25°C	4	All	37.5	42.5	kHz
Oscillator accuracy over temperature	F _{OSC} (OT)	T _A = -55°C and +125°C	5,6	All	35.2	44.8	kHz
Voltage stability	VSTAB	V _{IN} = 8 V to 35 V	4,5,6	All		±1	%
Clock pulse amplitude	Vosc	<u>3</u> /	4,5,6	All	3		V
Clock pulse width	tpW	T _A = +25°C <u>3</u> /	9	All	0.3	1.0	μS
Max oscillator frequency	F _{MAX}	$R_T = 2 \text{ k}\Omega, C_T = .001 \mu\text{F}$	4,5,6	01,02	300		kHz
		R_T = 2 kΩ, C_T = 470 μF		03,04	350		
				05	400		

See footnotes at end of table.

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	1	 	1	1 1			1
Test	Symbol	Conditions $\underline{1}/$ -55°C \leq T _A \leq +125°C unless otherwise specified	Group A subgroups	Device type	Lim	its <u>2</u> /	Unit
					Min	Max	
Oscillator section – contin	ued.	1	1	1		1	
Min oscillator frequency	F _{MIN}	$R_T = 150 \text{ k}\Omega, C_T = 0.1 \mu\text{F}$	4,5,6	01,02		150	Hz
		R_T = 200 kΩ, C_T = 0.1 μF	1	03,04, 05		120	
Threshold SYNC voltage	V _{TH} (SYNC)		1,2,3	All	1.2	2.8	V
SYNC input current	I _I (SYNC)	SYNC voltage = 3.5 V	1,2,3	All		2.5	mA
Pulse width modulator co	mparator section	n	•				
Min duty cycle	t _{ON} (min) /	V _{COMP} = 0.6 V	9,10,11	01-04		.001	%
	tosc			05		0	1
Max duty cycle	t _{ON} (max) /	V _{COMP} = 3.6 V	9,10,11	All	45		%
	tosc						
Error amplitude section, \	/ _{CM} = 5.1 V (ur	nless otherwise specified)					
Input offset voltage	V _{IO}	$R_S \le 2 k\Omega$	1,2,3	All	-5	5	mV
Input bias current	I _{IB}		1,2,3	All		10	μА
Input offset current	lio		1,2,3	All	-1	1	μА
DC open loop gain	A _{VOL}	$T_A = +25^{\circ}C$, $V_{CM} = 5.1 \text{ V}$, $R_L \ge 10 \text{ M}\Omega$	4	All	60		dB
Output low level	V _{OL}		1,2,3	All		0.5	V
Output high level	V _{OH}		1,2,3	All	3.8		V
Common mode rejection ratio	CMRR	V _{CM} = 1.5 V to 5.2 V	1,2,3	All	60		dB
Power supply rejection ratio	PSRR	V _{IN} = 8 V to 35 V	4,5,6	All	50		dB

See footnotes at end of table.

GBW

Unity gain bandwidth

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 $A_V = 0 \text{ dB}, T_A = +25^{\circ}C \ \underline{3}/$

All

1

MHz

	TABLE	I. Electrical performance chara	acteristics – Co	ntinued.			
Test			Device type	· · · · · —		Unit	
					Min	Max	
Soft start section	<u> </u>		•	1		1	+
Soft start current	ISS	$V_{SD} = 0 V$, $V_{SS} = 0 V$	1,2,3	All	25	80	μΑ
Soft start voltage	V _{SS}	V _{SD} = 2.5 V	1,2,3	All		0.7	V
Shutdown input current	I _{SD}	V _{SD} = 2.5 V	1,2,3	All		1.0	mA
Shutdown threshold voltage	V _{TH}	To outputs, $V_{SS} = 5.1 \text{ V}$, $T_A = +25^{\circ}\text{C}$	4	03,04, 05	0.6		V
Output section (each out	out), V _C = +20	V (unless otherwise specified)					
Output low level	V _{OL}	I _{SINK} = 20 mA	1,2,3	All		0.4	V
		I _{SINK} = 100 mA				2.2	
Output high level	Voн	ISOURCE = -20 mA	1,2,3	All	18		V
		ISOURCE = -100 mA			17		
Under voltage lockout	V _{UL}	V _{COMP} and V _{SS} = high	1,2,3	All	6	8	V
Shutdown delay	tsD	V _{SD} = 3 V, T _A = +25°C <u>3</u> /	9	01,02		500	ns
		V _{SD} = 2.5 V, T _A = +25°C <u>3</u> /		03,04, 05		500	
Rise time	t _r	$C_L = 1 \text{ nF}, T_A = +25^{\circ}C \ \underline{3}/$	9	All		600	ns
Collector fall time	tf	$C_L = 1 \text{ nF}, T_A = +25^{\circ}C \ \underline{3}/$	9	All		300	ns
Collector leakage voltage	V _{CL}	V _C = 35 V	1,2,3	05		200	μА
V _C off current	I _{VC}	V _C = 35 V	1,2,3	01,03		200	μА
Total standby current sec	` ,						1
Supply current	Is	V _{IN} = 35 V	1,2,3	All		20	mA

 $[\]underline{1}/$ Unless otherwise specified, +V_IN = 20 V, RT = 3.6 k $\Omega,$ CT = 0.01 $\mu F,$ and RD = 0 $\Omega.$

 $\underline{3}$ / If not tested, shall be guaranteed to the limits specified in table I herein.

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^{2/} The algebraic convention, whereby the most negative value is a minimum and the most positive is a maximum, is used in this table. Negative current shall be defined as conventional current flow out of a device terminal.

Device types	01,02,03,04, and 05			
Case outlines	E and F	2		
Terminal number	Terminal	symbol		
1	INVERTING INPUT	NC		
2	NONINVERTING INPUT	INVERTING INPUT		
3	SYNC	NONINVERTING INPUT		
4	OSCILLATOR OUTPUT	SYNC		
5	C _T	OSCILLATOR OUTPUT		
6	R _T	NC		
7	DISCHARGE	CT		
8	SOFT-START	R _T		
9	COMPENSATION	DISCHARGE		
10	SHUTDOWN	SOFT START		
11	OUTPUT A	NC		
12	GROUND	COMPENSATION		
13	Vc	SHUTDOWN		
14	OUTPUT B	OUTPUT A		
15	+V _{IN}	GROUND		
16	V _{REF}	NC		
17		Vc		
18		OUTPUT B		
19		+V _{IN}		
20		V _{REF}		

NC = No connection

FIGURE 1. Terminal connections.

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Device types 01 and 02

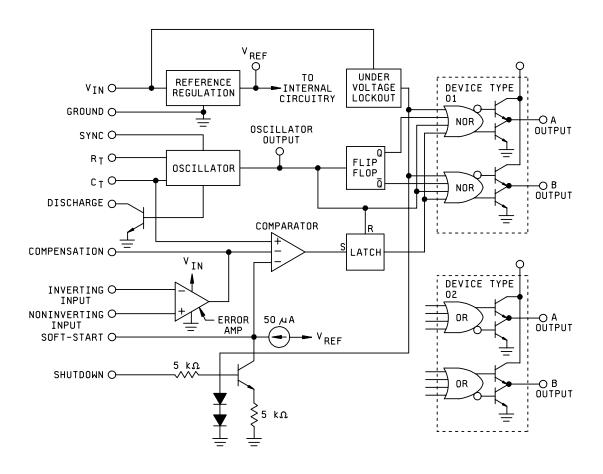


FIGURE 2. Logic diagram.

	1		
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Device types 03 and 04

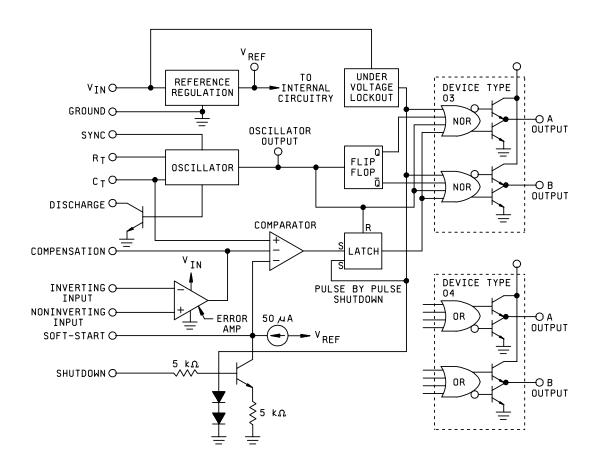


FIGURE 2. Logic diagram - Continued.

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Device type 05

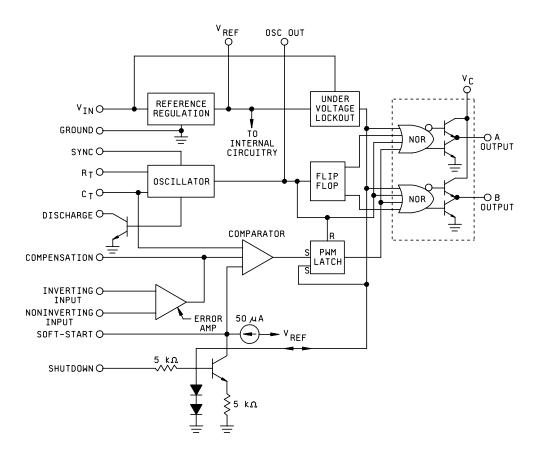


FIGURE 2. Logic diagram - Continued.

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- 3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change for device class M</u>. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change that affects this drawing.
- 3.9 <u>Verification and review for device class M.</u> For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 110 (see MIL-PRF-38535, appendix A).

4. VERIFICATION

- 4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.
- 4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.
 - 4.2.1 Additional criteria for device class M.
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table II herein.
 - 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table II herein.
 - Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

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TABLE II. Electrical test requirements.

Test requirements	Subgroups	Subgroups	
	(in accordance with	(in accordance with	
	MIL-STD-883,	MIL-PRF-385	35, table III)
	method 5005, table I)		
	Device	Device	Device
	class M	class Q	class V
Interim electrical			
parameters (see 4.2)			
Final electrical	1,2,3,4,9 <u>1</u> /	1,2,3,4,9 <u>1</u> /	1,2,3,4,9 <u>1</u> /
parameters (see 4.2)			
Group A test	1,2,3,4,5,6,	1,2,3,4,5,6,	1,2,3,4,5,6,
requirements (see 4.4)	7,9,10,11	7,9,10,11	7,9,10,11
Group C end-point electrical	1	1	1,2,3
parameters (see 4.4)			
Group D end-point electrical	1	1	1,2,3
parameters (see 4.4)			
Group E end-point electrical			
parameters (see 4.4)			

^{1/} PDA applies to subgroup 1.

- 4.3 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
- 4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
 - 4.4.1 Group A inspection.
 - a. Tests shall be as specified in table II herein.
 - b. Subgroup 8 in table I, method 5005 of MIL-STD-883 shall be omitted.
 - 4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table II herein.
 - 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
 - b. $T_A = +125$ °C, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

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- 4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
 - 4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.
- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).
 - a. End-point electrical parameters shall be as specified in table II herein.
 - b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C, after exposure, to the subgroups specified in table II herein.

5. PACKAGING

- 5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.
 - 6. NOTES
- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.
- 6.3 <u>Record of users</u>. Military and industrial users should inform Defense Supply Center Columbus (DSCC) when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0525.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0547.
- 6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.
 - 6.6 Sources of supply.
- 6.6.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.
- 6.6.2 <u>Approved sources of supply for device class M.</u> Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

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DATE: 06-03-13

Approved sources of supply for SMD 5962-89511 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DSCC maintains an online database of all current sources of supply at http://www.dscc.dla.mil/Programs/Smcr/.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /	Reference military specification PIN
5962-8951101EA	U3158	IP1525AJ/883B	M38510/12602BEA
	01295	UC1525AJ/883B	
	34333	SG1525AJ/883B	
	<u>3</u> /	LT1525AJ/883	
5962-8951101FA	34333	SG1525AF/883B	
5962-89511012A	01295	UC1525AL/883B	
5962-8951102EA	U3158	IP1527AJ/883B	M38510/12604BEA
	01295	UC1527AJ/883B	
	34333	SG1527AJ/883B	
	<u>3</u> /	LT1527AJ/883	
5962-89511022A	01295	UC1527AL/883B	
5962-8951103EA	01295	UC1525AJ/883B	
5962-89511032A	01295	UC1525AL/883B	
5962-8951103VEA	<u>3</u> /	UC1525AJQMLV	
5962-8951103V2A	<u>3</u> /	UC1525ALQMLV	

STANDARD MICROCIRCUIT DRAWING B'ULLETIN - CONTINUED

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /	Reference military specification PIN
5962-8951104EA	01295	UC1527AJ/883B	
5962-89511042A	01295	UC1527AL/883B	
5962-8951105EA	01295	UC1525BJ/883B	
5962-89511052A	01295	UC1525BL/883B	
5962-8951105VEA	01295	UC1525BJQMLV	
5962-8951105V2A	01295	UC1525BLQMLV	

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- 2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
- 3/ Not available from an approved source of supply.

Vendor CAGE number	Vendor name and address
U3158	Semelab PLC Coventry Road, Lutterworth Leicestershire, LE174JB United Kingdom
01295	Texas Instruments, Incorporated Semiconductor Group 8505 Forest Lane P.O. Box 660199 Dallas, TX 75243 Point of contact: U.S. Highway 75 South P.O. Box 84, M/S 853 Sherman, TX 75090-9493
34333	Microsemi Integrated Products 11861 Western Avenue

Garden Grove, CA 92641

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.